L Number	Hits	Search Text	DB	Time stamp
-	2510	composite near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:53
-	94	(composite near dielectric) and (effective near dielectric near constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:01
-	2	((composite near dielectric) and (effective near dielectric near constant)) and (dielectric with ((cubic near boron near nitride) CBN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 19:19
-	33	(dielectric with ((cubic near boron near nitride) CBN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:04
-	2	("6674146").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:01
-	1	"5081053".PN.	USPAT	2004/08/04 07:41
-	5783	((contact near point$1) gate junction interconnect$3) near2 surface near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:04
-	57	(((contact near point$1) gate junction interconnect$3) near2 surface near2 substrate) and ((boron near nitride) CBN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:38
-	49	composite near dielectric and ((boron near nitride) CBN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:13
-	791	dielectric with ((boron near nitride) CBN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:59
-	3	(dielectric with ((boron near nitride) CBN)) and (((contact near point$1) gate junction interconnect$3) near2 surface near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:59
-	1331	dielectric same ((boron near nitride) CBN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:59
-	5	(dielectric same ((boron near nitride) CBN)) and (((contact near point$1) gate junction interconnect$3) near2 surface near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:59

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-	47	(dielectric same ((boron near nitride) CBN)) and (effective near dielectric near constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:01
-	6	09/607,207	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:39
-	8	dielectric near constant near Si3N4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:50
-	2	contact near composite near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:51
-	2	contact near through near2 composite near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:52
-	2	(contact near through near2 dielectric near (layer film)) and (composite near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:54
-	194	contact near through near2 dielectric near (layer film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 12:05
-	4	(contact near through near2 dielectric near (layer film)) and ((boron near nitride) CBN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 11:55
-	2	first near dielectric near surround$3 near second near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 12:08
-	15	first near (insulat$3 dielectric) near surround$3 near second near (insulat$3 dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 12:21
-	0	first near (insulat$3 dielectric) near2 ((boron near nitride) CBN) near surround$3 near second near (insulat$3 dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 12:20
-	41	first near (insulat$3 dielectric) near (cover$3 surround$3 around) near second near (insulat$3 dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 12:21